

## Applications

- Power Management in Desktop Computer or DC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial.

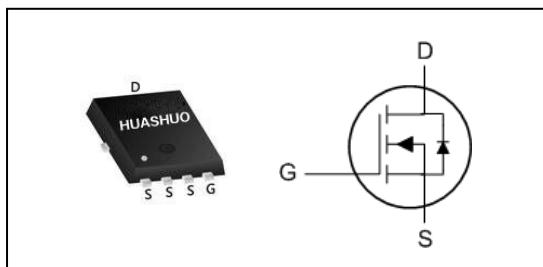
## Product Summary

V <sub>DS</sub>	30	V
R <sub>DSON,typ</sub>	3	mΩ
I <sub>D</sub>	75	A

## Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

## PRPAK5\*6 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>c</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1</sub>	75	A
I <sub>D</sub> @T <sub>c</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1</sub>	45	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	160	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	144	mJ
I <sub>AS</sub>	Avalanche Current	54	A
P <sub>D</sub> @T <sub>c</sub> =25°C	Total Power Dissipation <sup>4</sup>	50	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	50	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	2.5	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

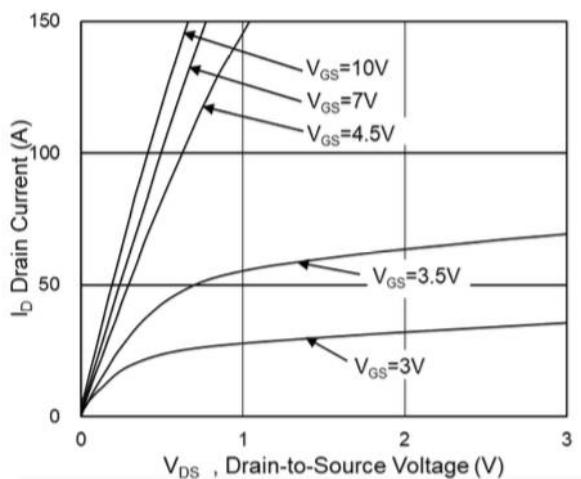
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30	---	---	V
△BV <sub>DSS</sub> /△T <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA	---	0.021	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A	---	3	3.8	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A	---	3.8	5.8	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.7	2.5	V
△V <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.73	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =20A	---	75	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =10V , V <sub>GS</sub> =0V , f=1MHz	---	1.7	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =20A	---	23	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	11	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	8.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V , R <sub>G</sub> =1.5Ω I <sub>D</sub> =20A	---	12.6	---	ns
T <sub>r</sub>	Rise Time		---	9.6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	55	---	
T <sub>f</sub>	Fall Time		---	5.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz	---	2461	---	pF
C <sub>oss</sub>	Output Capacitance		---	383	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	261	---	

**Diode Characteristics**

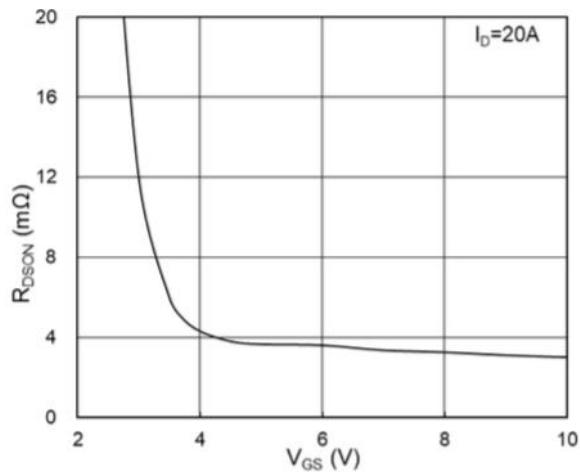
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>s</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	40	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>s</sub> =1A , T <sub>J</sub> =25°C	---	---	1	V

Note :

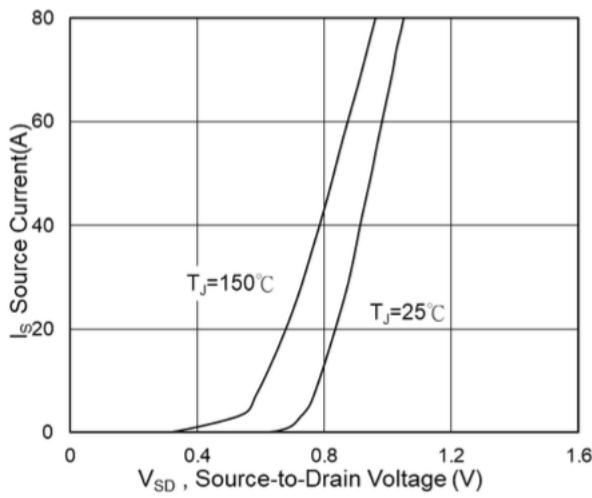
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=54A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



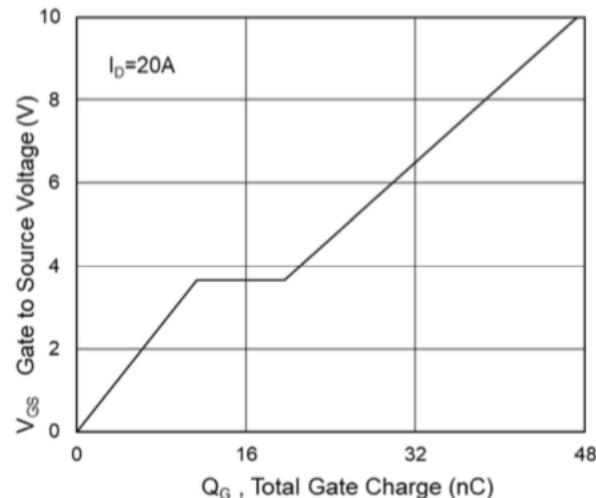
**Fig.1 Typical Output Characteristics**



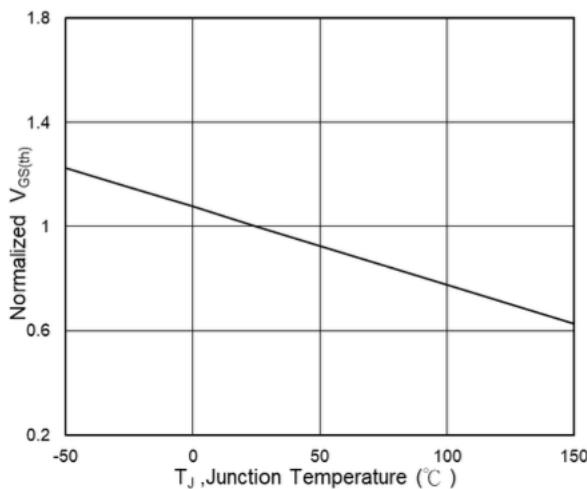
**Fig.2 On-Resistance vs. G-S Voltage**



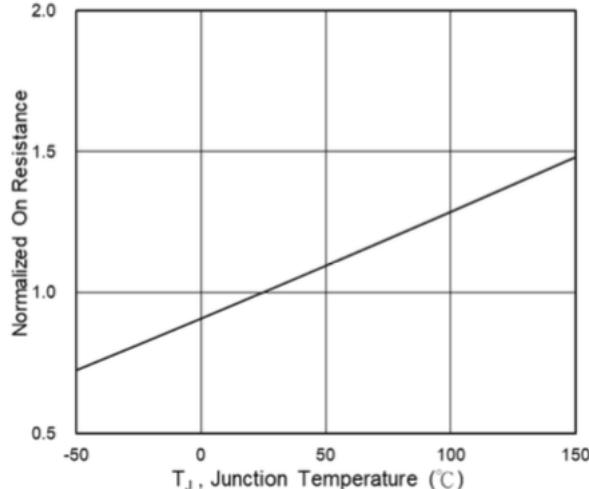
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

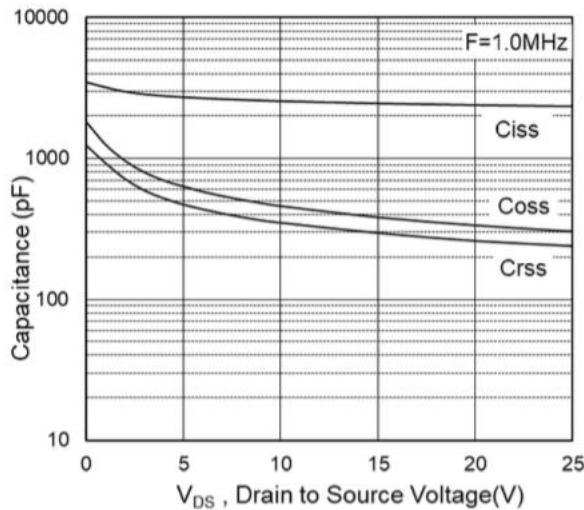


Fig.7 Capacitance

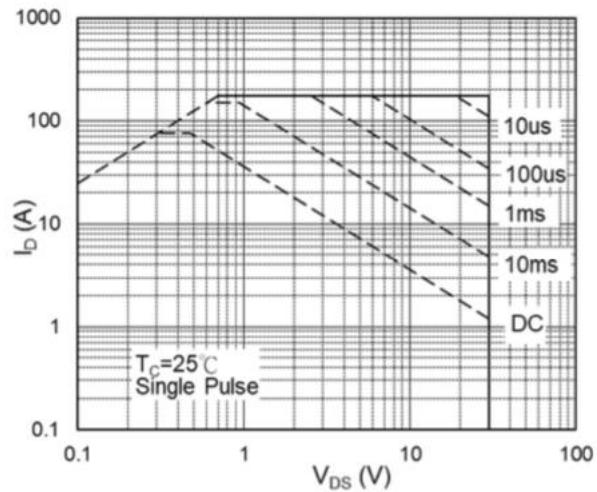


Fig.8 Safe Operating Area

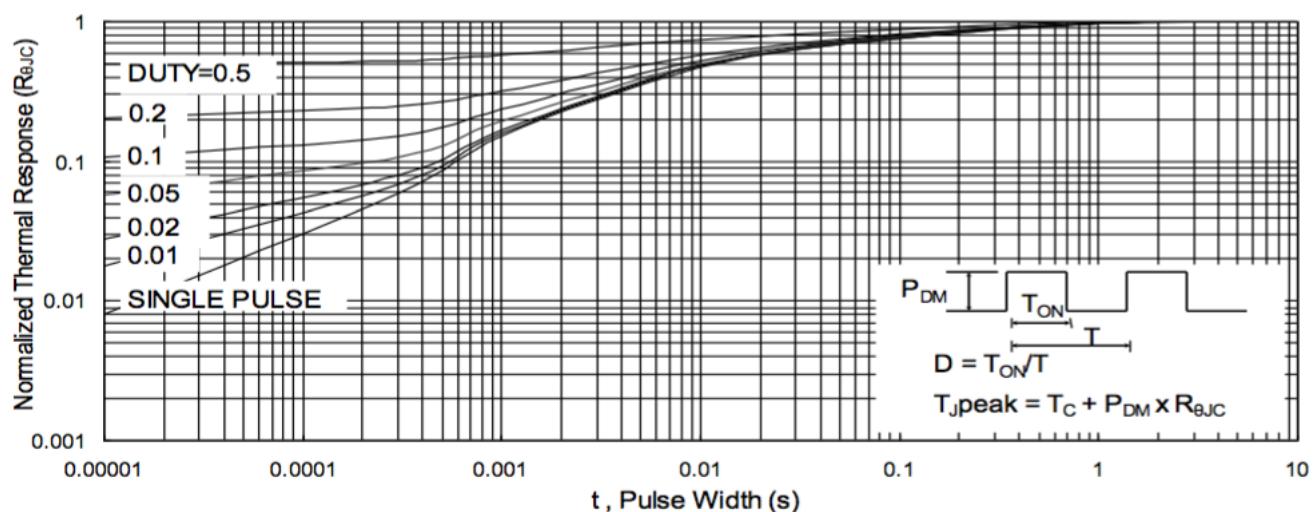


Fig.9 Normalized Maximum Transient Thermal Impedance

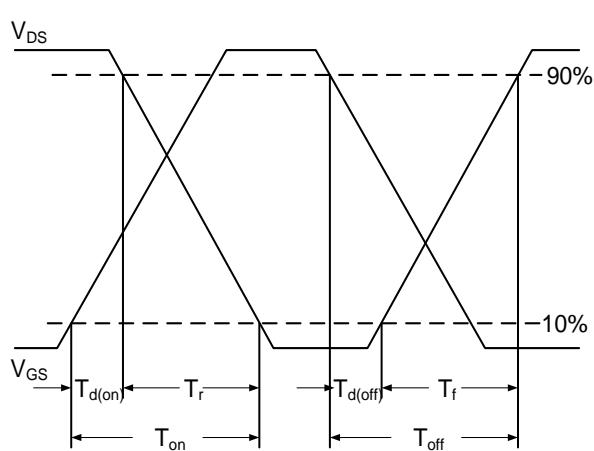


Fig.10 Switching Time Waveform

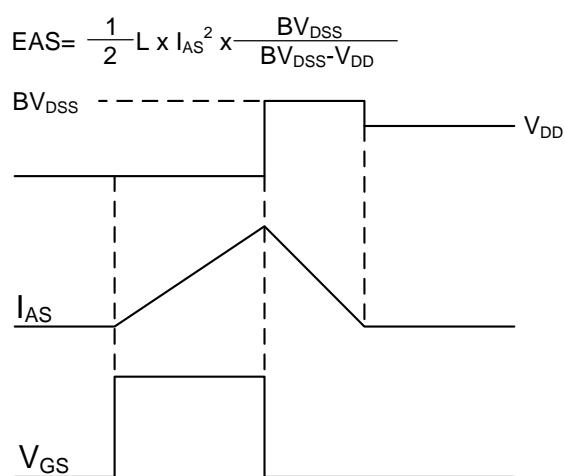


Fig.11 Unclamped Inductive Switching



## Ordering Information

Part Number	Package code	Packaging
HSBA3050	PRPAK5*6	3000/Tape&Reel

